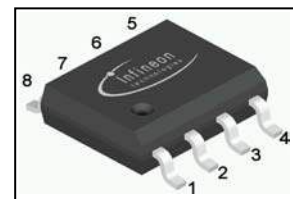


OptiMOS™-P Power-Transistor
Features

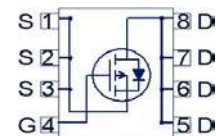
- P-Channel
- Enhancement mode
- Logic level
- 150°C operating temperature
- Avalanche rated
- dv/dt rated
- Ideal for fast switching buck converter

Product Summary

V_{DS}	-30	V
$R_{DS(on),max}$	13	mΩ
I_D	-11.3	A

P-DSO-8


Type	Package	Marking
BSO130P03S	P-DSO-8	130P3S


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value		Unit
			≤10 secs	steady state	
Continuous drain current	I_D	$T_A=25\text{ °C}^{1)}$	-11.3	-9.2	A
		$T_A=70\text{ °C}^{1)}$	-9.1	-7.4	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}^{2)}$	-45		
Avalanche energy, single pulse	E_{AS}	$I_D=11.3\text{ A}, R_{GS}=25\text{ Ω}$	148		mJ
Reverse diode dv/dt	dv/dt	$I_D=11.3\text{ A}, V_{DS}=20\text{ V},$ $di/dt=-200\text{ A/μs},$ $T_{j,max}=150\text{ °C}$	-6		kV/μs
Gate source voltage	V_{GS}		±25		V
Power dissipation	P_{tot}	$T_A=25\text{ °C}^{1)}$	2.36	1.56	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - soldering point	R_{thJS}		-	-	35	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm ² cooling area ¹⁾ , $t_p \leq 10$ s	-	-	53	
		6 cm ² cooling area ¹⁾ , steady state	-	-	80	

Electrical characteristics, at $T_j = 25$ °C, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -250$ μ A	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -140$ μ A	-1	-1.5	-2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -30$ V, $V_{GS} = 0$ V, $T_j = 25$ °C	-	-0.1	-1	μ A
		$V_{DS} = -30$ V, $V_{GS} = 0$ V, $T_j = 125$ °C	-	-10	-100	
Gate-source leakage current	I_{GSS}	$V_{GS} = -25$ V, $V_{DS} = 0$ V	-	-10	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -10$ V, $I_D = -11.3$ A	-	9.9	13.0	m Ω
Transconductance	g_{fs}	$ V_{DS} > 2 I_D R_{DS(on)max}$, $I_D = -9.5$ A	14	27	-	S

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μ m thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}$, $V_{DS}=-25\text{ V}$, $f=1\text{ MHz}$	-	2650	3520	pF
Output capacitance	C_{oss}		-	708	942	
Reverse transfer capacitance	C_{rss}		-	580	870	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-1\text{ A}$, $R_G=6\ \Omega$	-	13	20	ns
Rise time	t_r		-	16	24	
Turn-off delay time	$t_{d(off)}$		-	70	105	
Fall time	t_f		-	62	93	

Gate Charge Characteristics³⁾

Gate to source charge	Q_{gs}	$V_{DD}=-24\text{ V}$, $I_D=11.3\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$	-	-7	-9	nC
Gate charge at threshold	$Q_{g(th)}$		-	-3.7	-5.0	
Gate to drain charge	Q_{gd}		-	-21	-32	
Switching charge	Q_{sw}		-	-25	-36	
Gate charge total	Q_g		-	-61	-81	
Gate plateau voltage	$V_{plateau}$		-	-2.6	-	V
Output charge	Q_{oss}	$V_{DD}=-15\text{ V}$, $V_{GS}=0\text{ V}$	-	-22	-29	

Reverse Diode

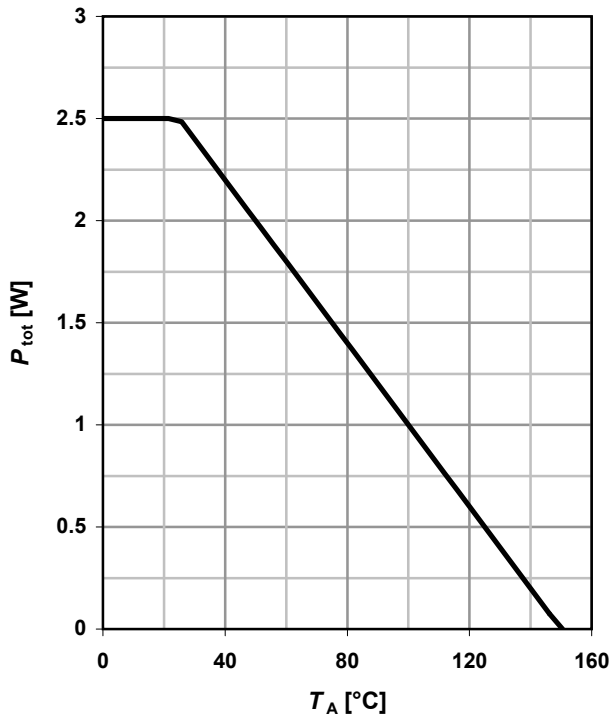
Diode continuous forward current	I_S	$T_A=25\text{ }^\circ\text{C}$	-	-	-2.1	A
Diode pulse current	$I_{S,pulse}$		-	-	-45	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}$, $I_F=-11.3\text{ A}$, $T_J=25\text{ }^\circ\text{C}$	-	-0.84	-1.2	V
Reverse recovery time	t_{rr}	$V_R=15\text{ V}$, $I_F=-11.3\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$	-	26	33	ns
Reverse recovery charge	Q_{rr}		-	16	20	nC

²⁾ See figure 3

³⁾ See figure 16 for gate charge parameter definition

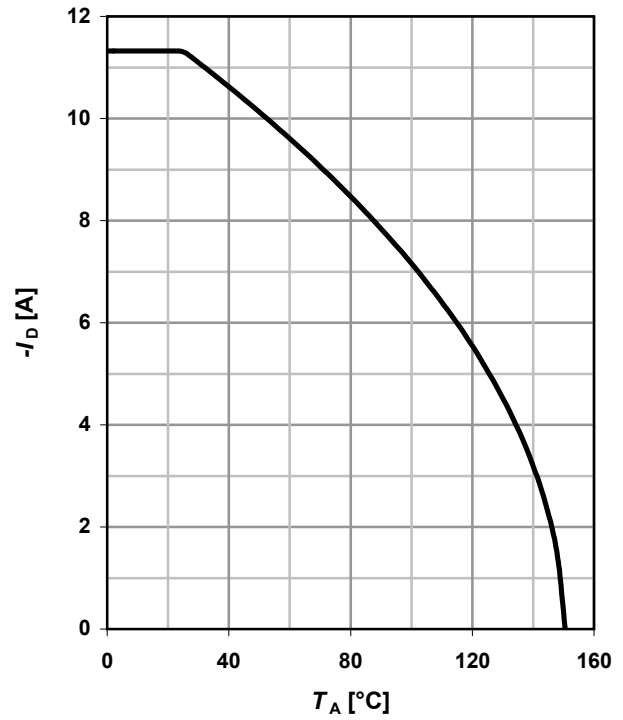
1 Power dissipation

$P_{tot}=f(T_A); t_p \leq 10 \text{ s}$



2 Drain current

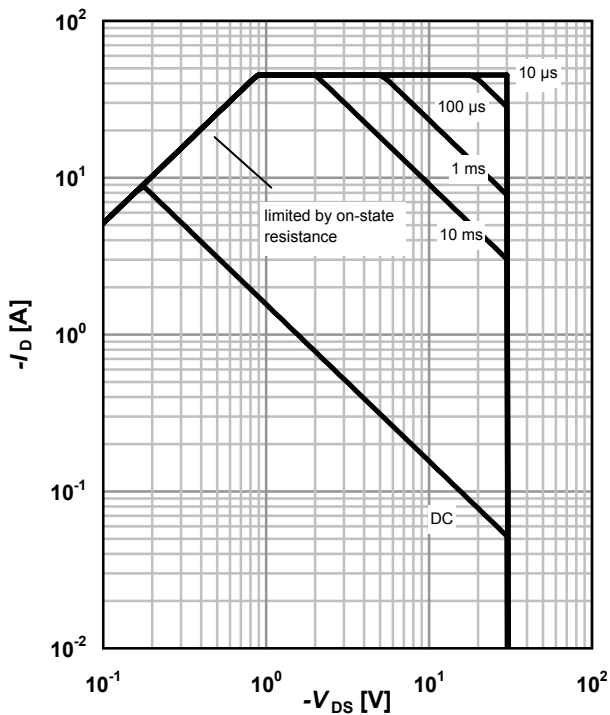
$I_D=f(T_A); |V_{GS}| \geq 10 \text{ V}; t_p \leq 10 \text{ s}$



3 Safe operating area

$I_D=f(V_{DS}); T_A=25 \text{ °C}^1; D=0$

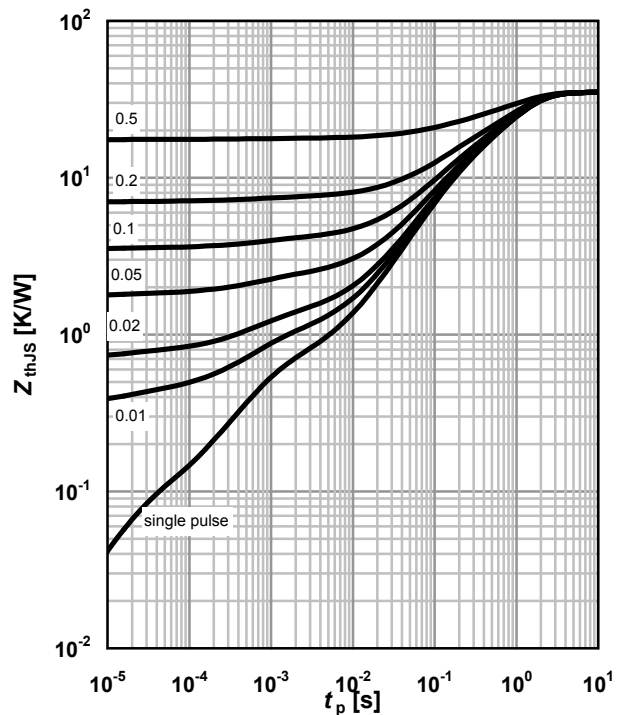
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJS}=f(t_p)$

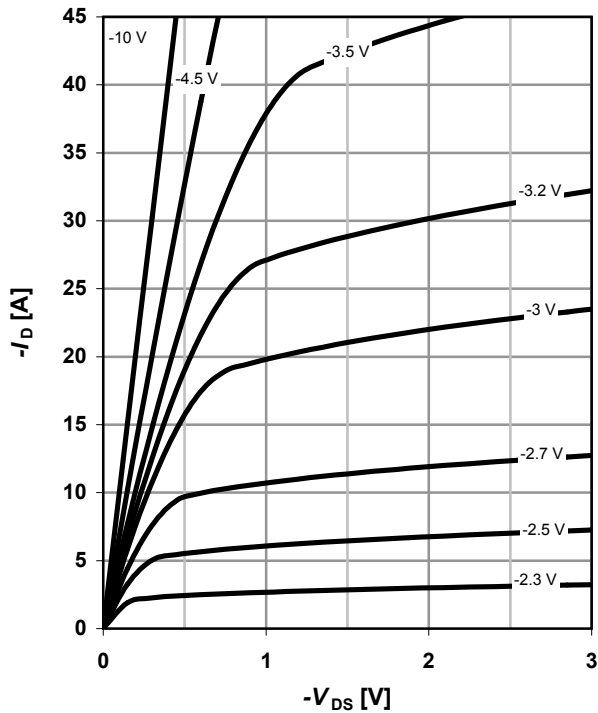
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

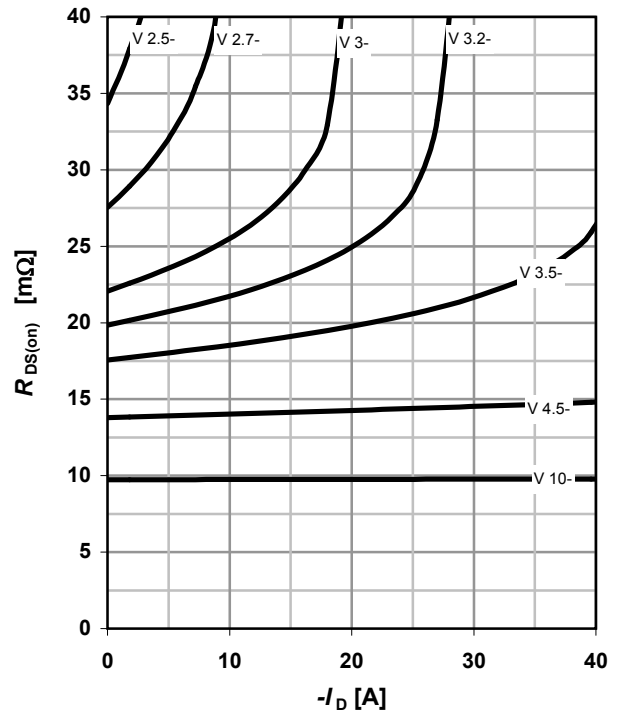
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

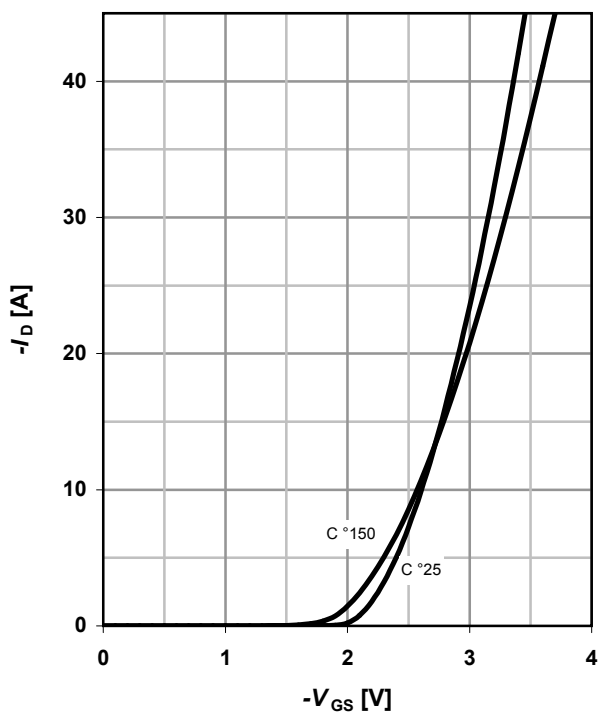
parameter: V_{GS}



7 Typ. transfer characteristics

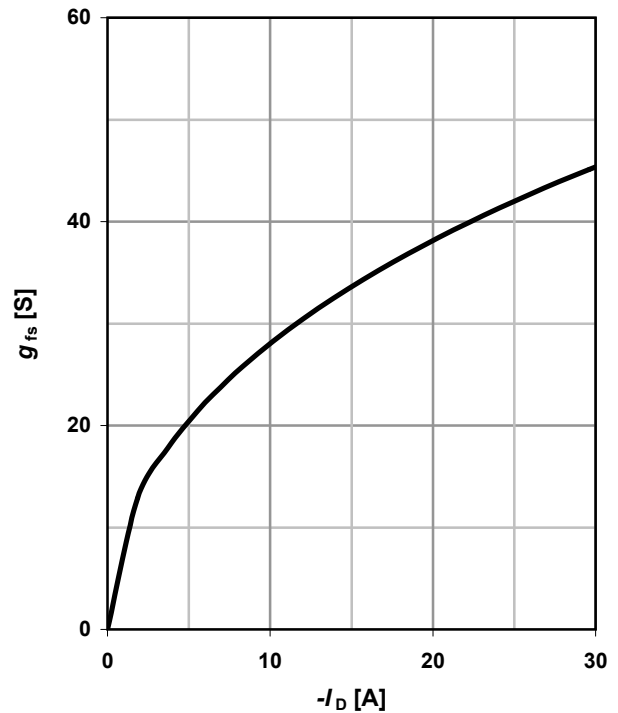
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



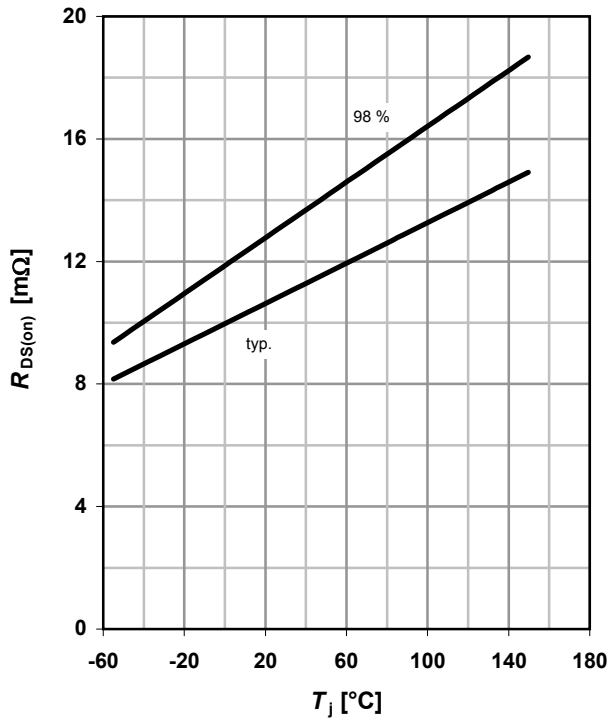
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



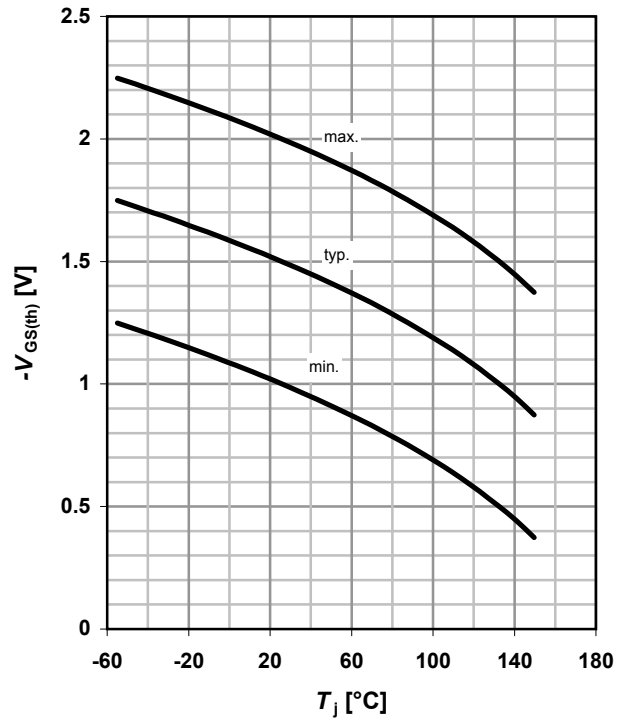
9 Drain-source on-state resistance

$R_{DS(on)}=f(T_j); I_D=-11.3\text{ A}; V_{GS}=-10\text{ V}$



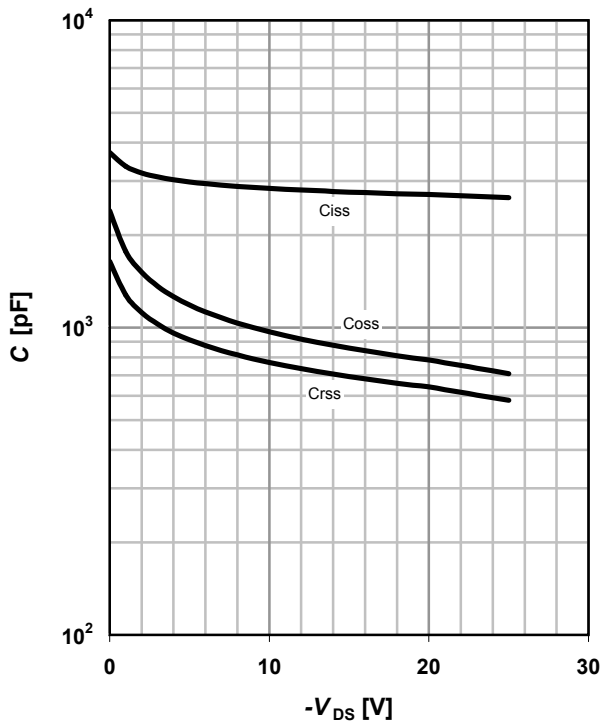
10 Typ. gate threshold voltage

$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}; I_D=-140\ \mu\text{A}$



11 Typ. capacitances

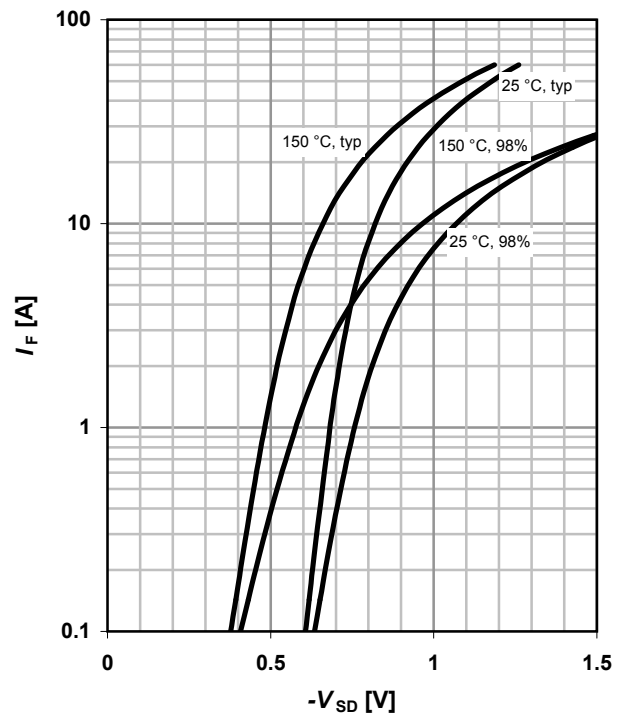
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



12 Forward characteristics of reverse diode

$I_F=f(V_{SD})$

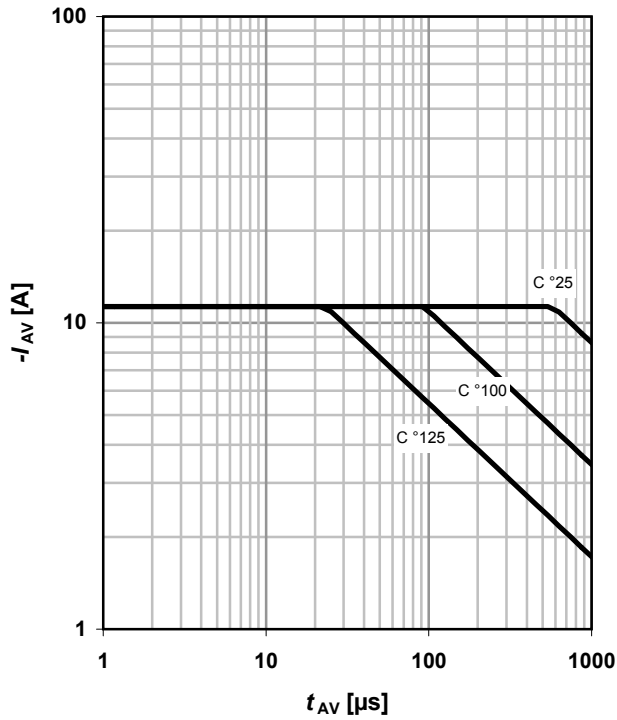
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

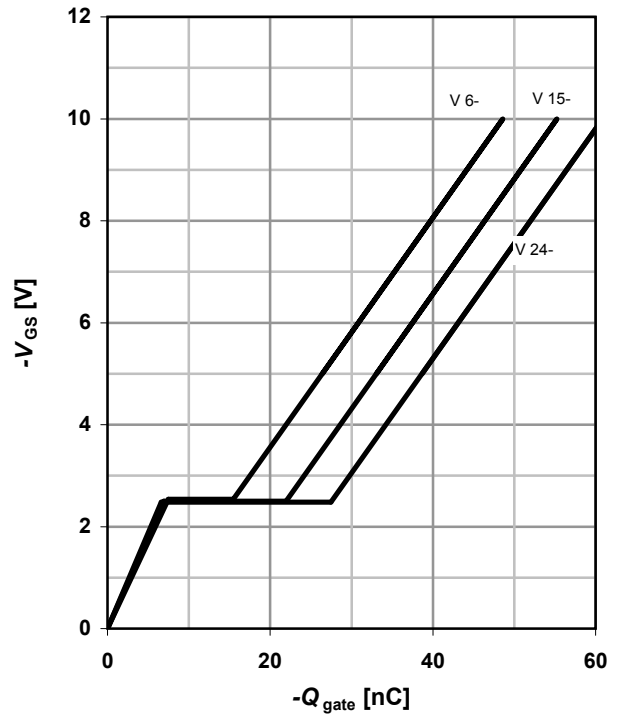
parameter: $T_{j(start)}$



14 Typ. gate charge

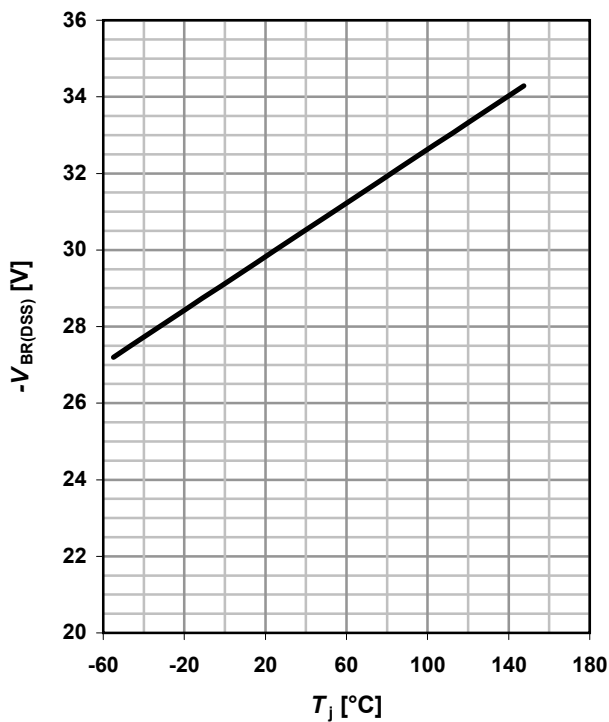
$V_{GS}=f(Q_{gate}); I_D=-5.5 \text{ A pulsed}$

parameter: V_{DD}

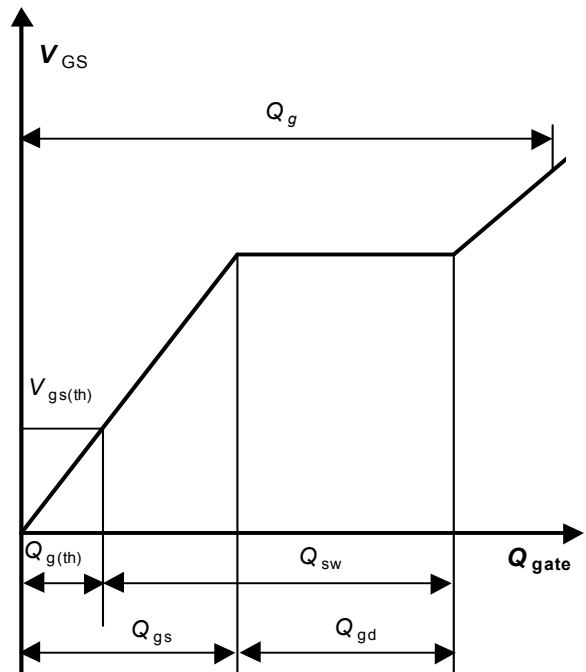


15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=-250 \mu\text{A}$

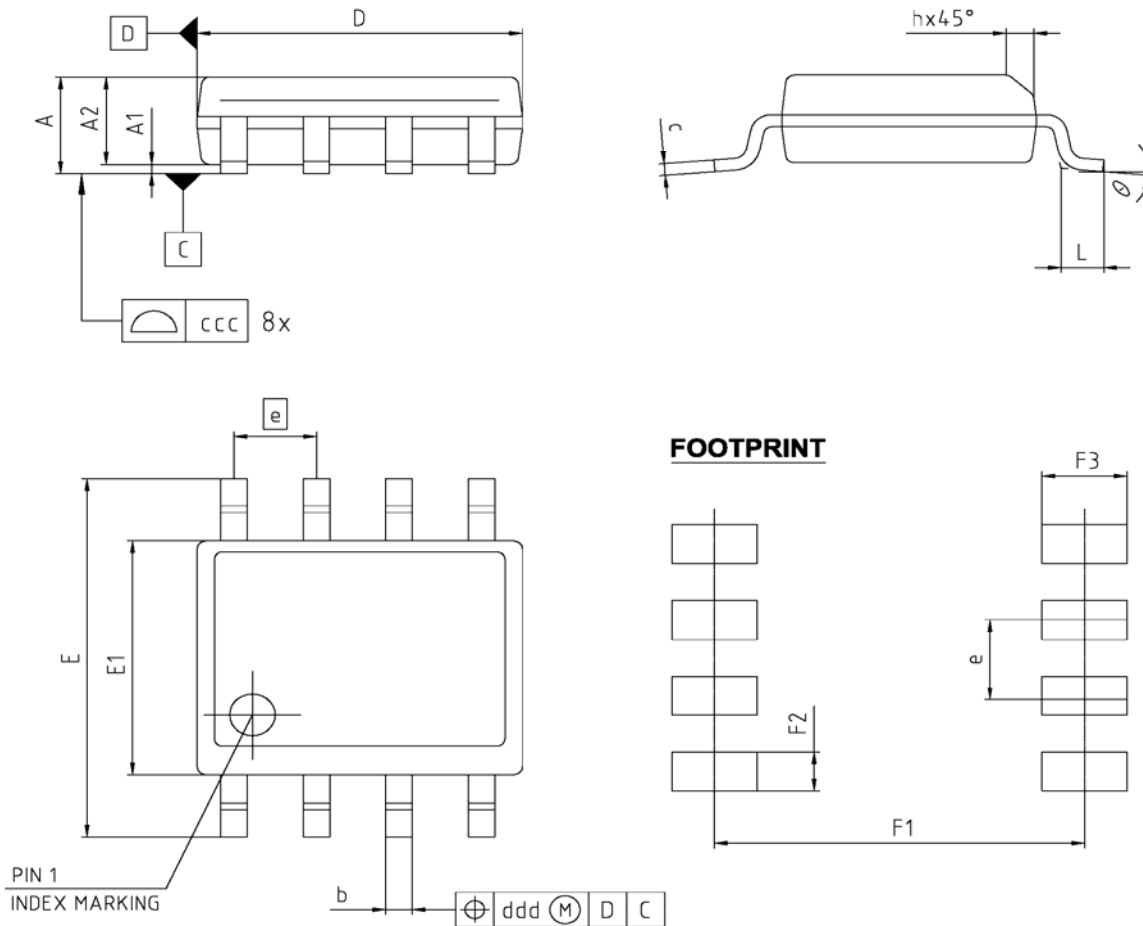


16 Gate charge waveforms



Package Outline

P-DSO-8: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.750	-	0.069
A1	0.100	-	0.004	-
A2	1.250	1.650	0.049	0.065
b	0.360	0.510	0.014	0.020
c	0.190	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
e	1.270		0.050	
N	8		8	
L	0.390	0.890	0.015	0.035
h	0.250	0.410	0.010	0.016
theta	0°		8°	
ccc	0.100		0.004	
ddd	0.200		0.008	
F1	5.590	5.790	0.220	0.228
F2	0.550	0.750	0.022	0.030
F3	1.210	1.410	0.048	0.056

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JEDEC / MS-012

SCALE

EUROPEAN PROJECTION

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